Old Company Name in Catalogs and Other Documents

On April 1st, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)
Send any inquiries to http://www.renesas.com/inquiry.



Notice

- 1. All information included in this document is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas Electronics products listed herein, please confirm the latest product information with a Renesas Electronics sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas Electronics such as that disclosed through our website.
- Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights
 of third parties by or arising from the use of Renesas Electronics products or technical information described in this document.
 No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights
 of Renesas Electronics or others.
- 3. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part.
- 4. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
- 5. When exporting the products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations. You should not use Renesas Electronics products or the technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations.
- 6. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
- 7. Renesas Electronics products are classified according to the following three quality grades: "Standard", "High Quality", and "Specific". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below. You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application categorized as "Specific" without the prior written consent of Renesas Electronics. Further, you may not use any Renesas Electronics product for any application for which it is not intended without the prior written consent of Renesas Electronics. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for an application categorized as "Specific" or for which the product is not intended where you have failed to obtain the prior written consent of Renesas Electronics. The quality grade of each Renesas Electronics product is "Standard" unless otherwise expressly specified in a Renesas Electronics data sheets or data books, etc.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; safety equipment; and medical equipment not specifically designed for life support.
 - "Specific": Aircraft; aerospace equipment; submersible repeaters; nuclear reactor control systems; medical equipment or systems for life support (e.g. artificial life support devices or systems), surgical implantations, or healthcare intervention (e.g. excision, etc.), and any other applications or purposes that pose a direct threat to human life.
- 8. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
- 9. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
- 10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 11. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written consent of Renesas Electronics
- 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.



MOS FIELD EFFECT TRANSISTOR



2SK2480

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK2480 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

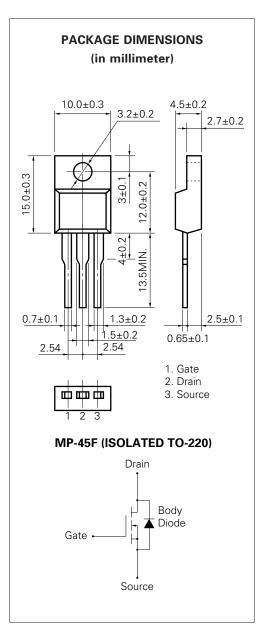
FEATURES

- Low On-Resistance
 RDS (on) = 4.0 Ω (VGS = 10 V, ID = 2.0 A)
- Low Ciss Ciss = 900 pF TYP.
- High Avalanche Capability Ratings
- Isolated TO-220 Package

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Drain to Source Voltage	V_{DSS}	900	V
Gate to Source Voltage	Vgss	±30	V
Drain Current (DC)	ID(DC)	±3.0	Α
Drain Current (pulse)*	ID(pulse	±12	Α
Total Power Dissipation ($T_c = 25$ °C)	P _{T1}	35	W
Total Power Dissipation (T _A = 25 °C)	P _{T2}	2.0	W
Channel Temperature	T_ch	150	°C
Storage Temperature	T_{stg}	–55 to +150	°C
Single Avalanche Current**	las	3.0	Α
Single Avalanche Energy**	Eas	37.1	mJ

- * PW \leq 10 μ s, Duty Cycle \leq 1 %
- ** Starting T_{ch} = 25 °C, R_G = 25 Ω , V_{GS} = 20 V \rightarrow 0





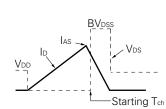


ELECTRICAL CHARACTERISTICS (TA = 25 °C)

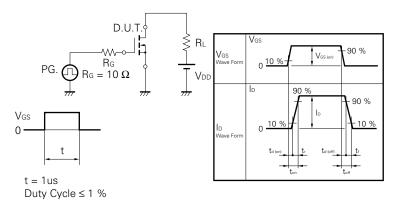
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	RDS (on)		3.2	4.0	Ω	Vgs = 10 V, ID = 2.0 A
Gate to Source Cutoff Voltage	VGS (off)	2.5		3.5	٧	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	l y _{fs} l	1.0			S	V _{DS} = 20 V, I _D = 2.0 A
Drain Leakage Current	Ipss			100	μΑ	V _{DS} = V _{DSS} , V _{GS} = 0
Gate to Source Leakage Current	Igss			±100	nA	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Input Capacitance	Ciss		900		pF	V _{DS} = 10 V
Output Capacitance	Coss		130		pF	V _G S = 0
Reverse Transfer Capacitance	Crss		25		pF	f = 1 MHz
Turn-On Delay Time	td (on)		17		ns	ID = 2.0 A
Rise Time	tr		7		ns	V _{GS} = 10 V
Turn-Off Delay Time	td (off)		63		ns	V _{DD} = 150 V
Fall Time	tf		8		ns	$R_G = 75 \Omega$
Total Gate Charge	Q G		30		nC	ID = 3.0 A
Gate to Source Charge	Qgs		5		nC	V _{DD} = 450 V
Gate to Drain Charge	QgD		16		nC	V _{GS} = 10 V
Body Diode Forward Voltage	VF (S-D)		1.0		V	IF = 3.0 A, VGS = 0
Reverse Recovery Time	trr		650		ns	IF = 3.0 A, VGS = 0
Reverse Recovery Charge	Qrr		2.8		μC	di/dt = 50 A/μs

Test Circuit 1 Avalanche Capability

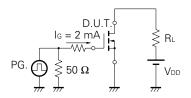
$V_{GS} = 20 - 0 \text{ V}$ $PG \longrightarrow 50 \Omega$ $V_{D} \longrightarrow 70 \text{ V}$ $V_{D} \longrightarrow 70 \text{ V}$



Test Circuit 2 Switching Time



Test Circuit 3 Gate Charge



The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

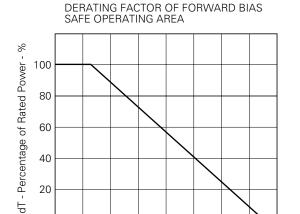
0

20

40

60

TYPICAL CHARACTERISTICS (TA = 25 °C)





80

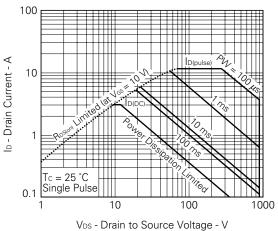
Tc - Case Temperature - °C

100

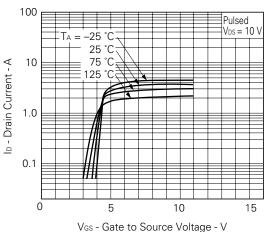
120

140

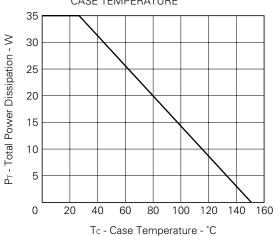
160



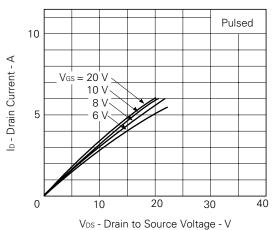
FORWARD TRANSFER CHARACTERISTICS



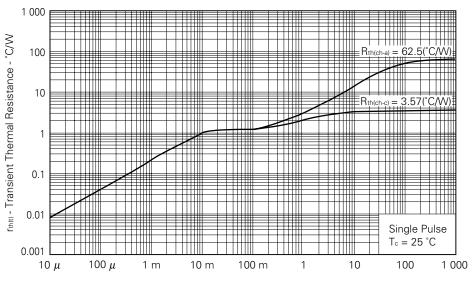
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

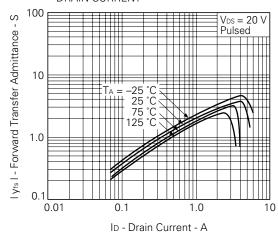


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

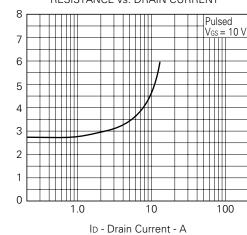


PW - Pulse Width - s

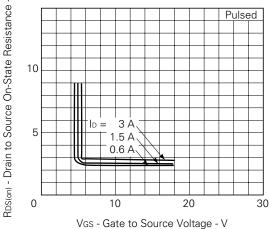
FORWARD TRANSFER ADMITTANCE vs. **DRAIN CURRENT**

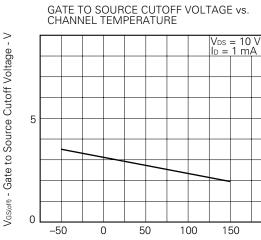


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



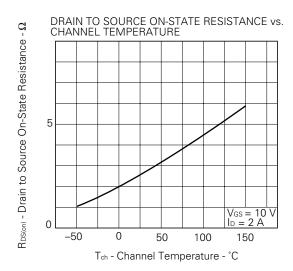
DRAIN TO SOURCE ON-STATE RESISTANCE vs. C GATE TO SOURCE VOLTAGE

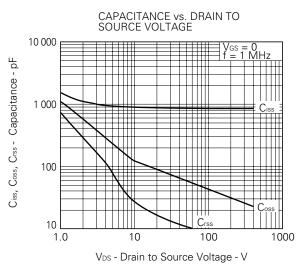


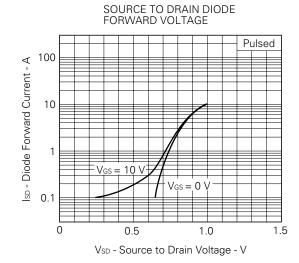


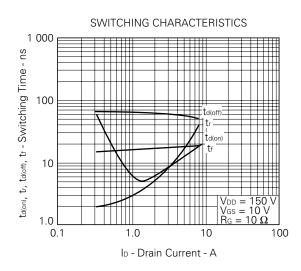
 T_ch - Channel Temperature - $^\circ\mathsf{C}$

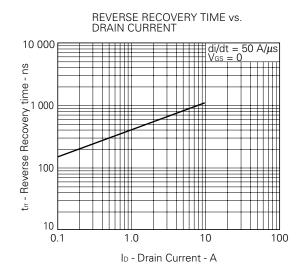
 $\mathsf{R}^{_{\mathsf{DS(on)}}}\text{-}\mathsf{Drain}$ to Source On-State Resistance - Ω

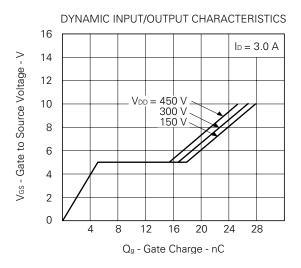




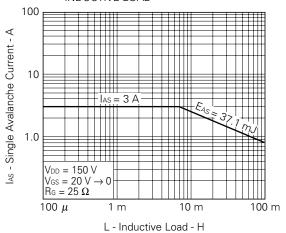




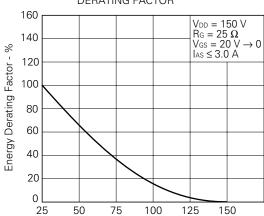




SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting T_{ch} - Starting Channel Temperature - $^{\circ}\text{C}$



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037



[MEMO]

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customer must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices in "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact NEC Sales Representative in advance.

Anti-radioactive design is not implemented in this product.